



**THE DATASHEET OF  
NCR125W-125MX**



## 1. General description

Planar passivated SCR with sensitive gate in a SOT223 surface mountable plastic package. This SCR is designed to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

## 2. Features and benefits

- Sensitive gate
- High surge current capability
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Direct triggering from low power drivers and logic ICs
- Surface mountable package

## 3. Applications

- Ground Fault Circuit Interrupter (GFCI)
- GFCI Socket
- Residual Current Circuit Breaker with Overcurrent Protection (RCBO)
- Arc Fault Circuit Interrupter (AFCI)

## 4. Quick reference data

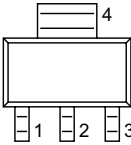

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values	Unit
$V_{DRM}$	repetitive peak off-state voltage		1250	V
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_c \leq 111\text{ }^\circ\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	1.25	A
$I_{TSM}$	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25\text{ }^\circ\text{C}$ ; $t_p = 10\text{ ms}$ ; <a href="#">Fig 4</a> ; <a href="#">Fig 5</a>	20	A
		half sine wave; $T_{j(init)} = 25\text{ }^\circ\text{C}$ ; $t_p = 8.3\text{ ms}$	22	A
$T_j$	junction temperature		125	$^\circ\text{C}$

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $R_L = 140\ \Omega$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>	1	-	100	$\mu\text{A}$
$I_H$	holding current	$V_D = 12\text{ V}$ ; $R_{GK} = 220\ \Omega$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>	-	-	10	mA
$V_T$	on-state voltage	$I_T = 2.5\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>	-	-	1.5	V
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 838\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; $R_{GK} = 220\ \Omega$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform	200	-	-	V/ $\mu\text{s}$

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		
2	A	anode		
3	G	gate		
4	A	mounting base; connected to anode		

## 6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
NCR125W-125M	SOT223	NCR125W-125MX	Reel	1000	SOT223	16-Mar-2006

## 7. Marking

Table 4. Marking codes

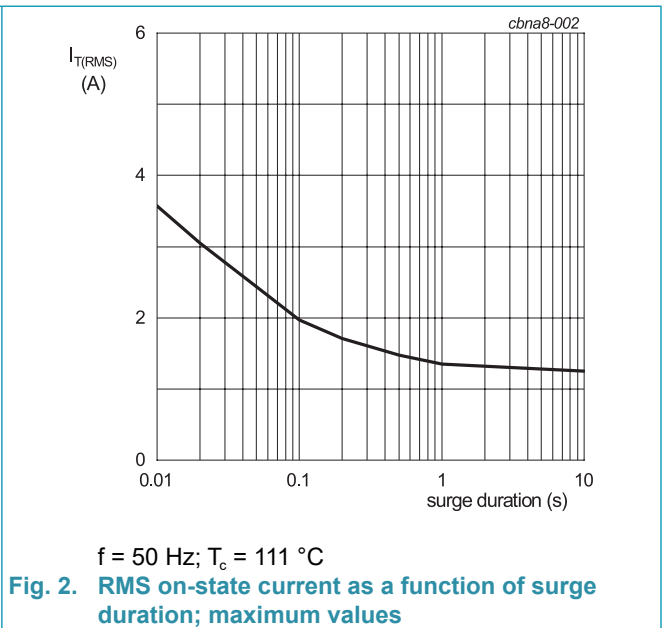
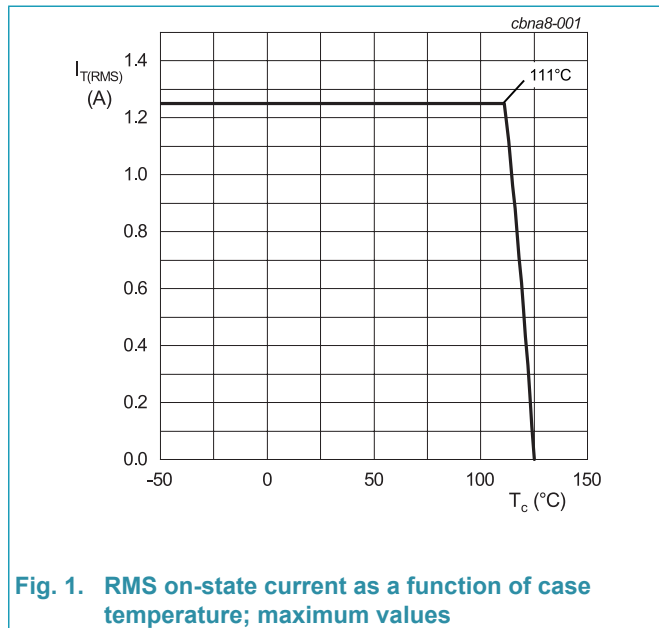
Type number	Marking codes
NCR125W-125M	125-125M

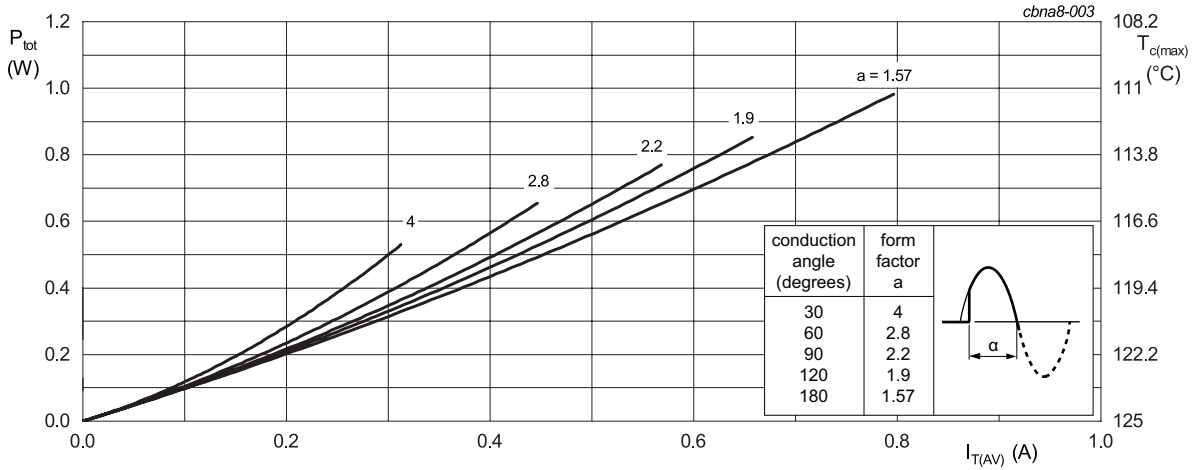
## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

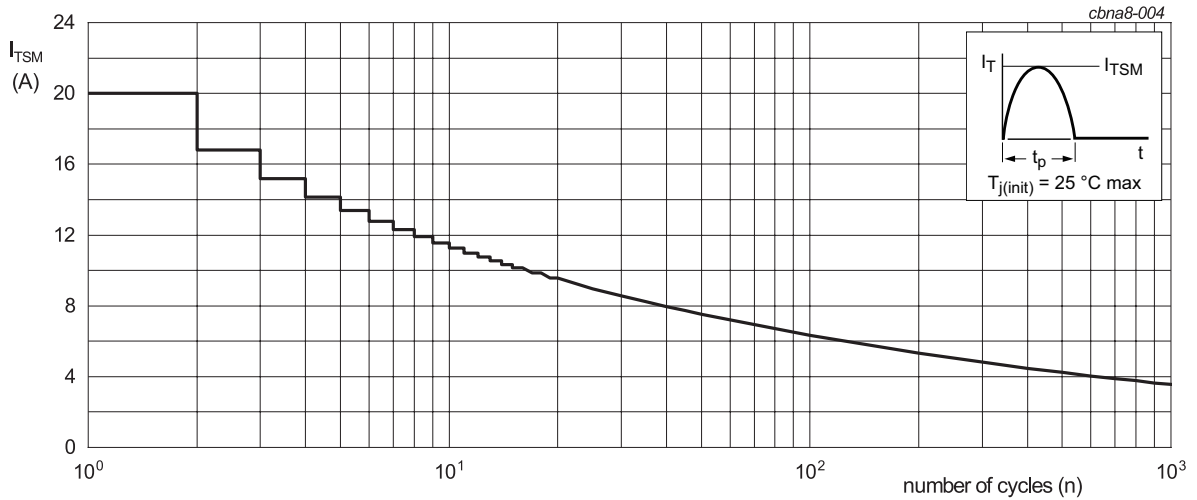
Symbol	Parameter	Conditions	Values	Unit
$V_{DRM}$	repetitive peak off-state voltage		1250	V
$V_{RRM}$	repetitive peak reverse voltage		1250	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_c \leq 111\text{ }^\circ\text{C}$ ;	0.8	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_c \leq 111\text{ }^\circ\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	1.25	A
$I_{TSM}$	non-repetitive peak on-state current	half sine wave; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; $t_p = 10\text{ ms}$ ; <a href="#">Fig 4</a> ; <a href="#">Fig 5</a>	20	A
		half sine wave; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; $t_p = 8.3\text{ ms}$	22	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$ ; sine-wave pulse	2	$\text{A}^2\text{s}$
$di_T/dt$	rate of rise of on-state current	$I_G = 0.1\text{ mA}$ ; $f = 50\text{ Hz}$ ; $T_j = 125\text{ }^\circ\text{C}$	100	$\text{A}/\mu\text{s}$
	non-repetitive critical current rate of rise at break over, refer <a href="#">Fig. 14</a>		200	$\text{A}/\mu\text{s}$
$I_{GM}$	peak gate current	$t_p = 20\text{ }\mu\text{s}$ ; $T_j = 125\text{ }^\circ\text{C}$	1.2	A
$P_{GM}$	peak gate power		5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	0.2	W
$T_{stg}$	storage temperature		-40 to 150	$^\circ\text{C}$
$T_j$	junction temperature		-40 to 125	$^\circ\text{C}$





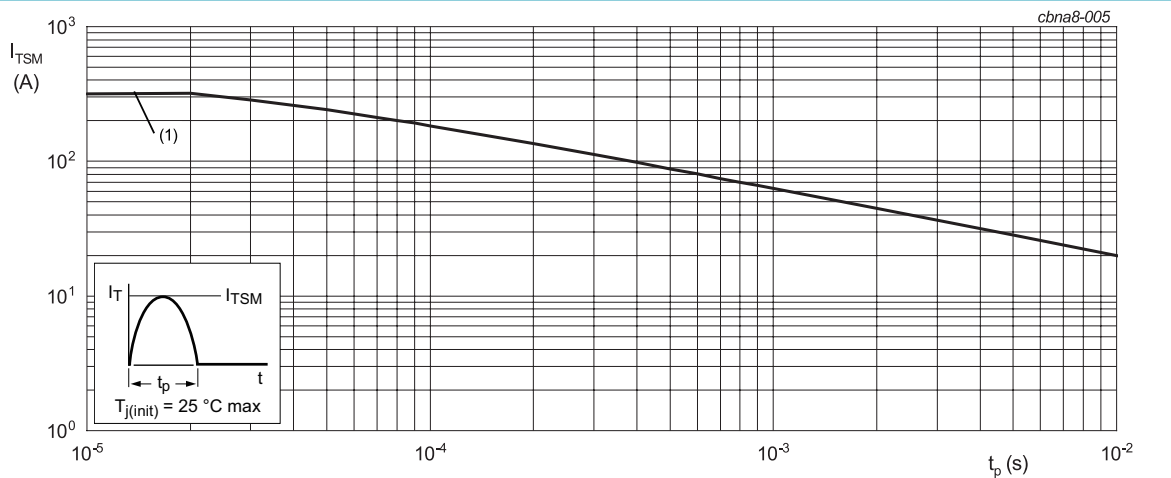
$\alpha$  = conduction angle  
 $a$  = form factor =  $I_{T(RMS)} / I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



$t_p \leq 10$  ms  
 (1)  $di_T/dt$  limit

Fig. 5. Non-repetitive peak on-state current as a function of pulse duration; maximum values

## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	<a href="#">Fig 6</a>	-	-	14	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air; printed circuit board mounted: minimum footprint; <a href="#">Fig 7</a>	-	130	-	K/W

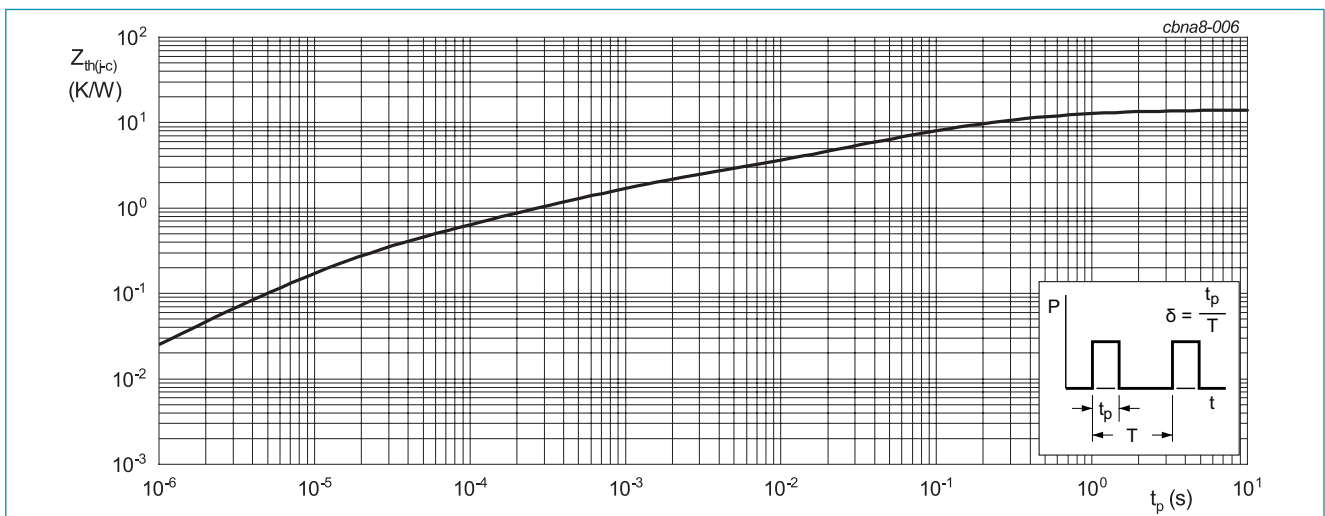
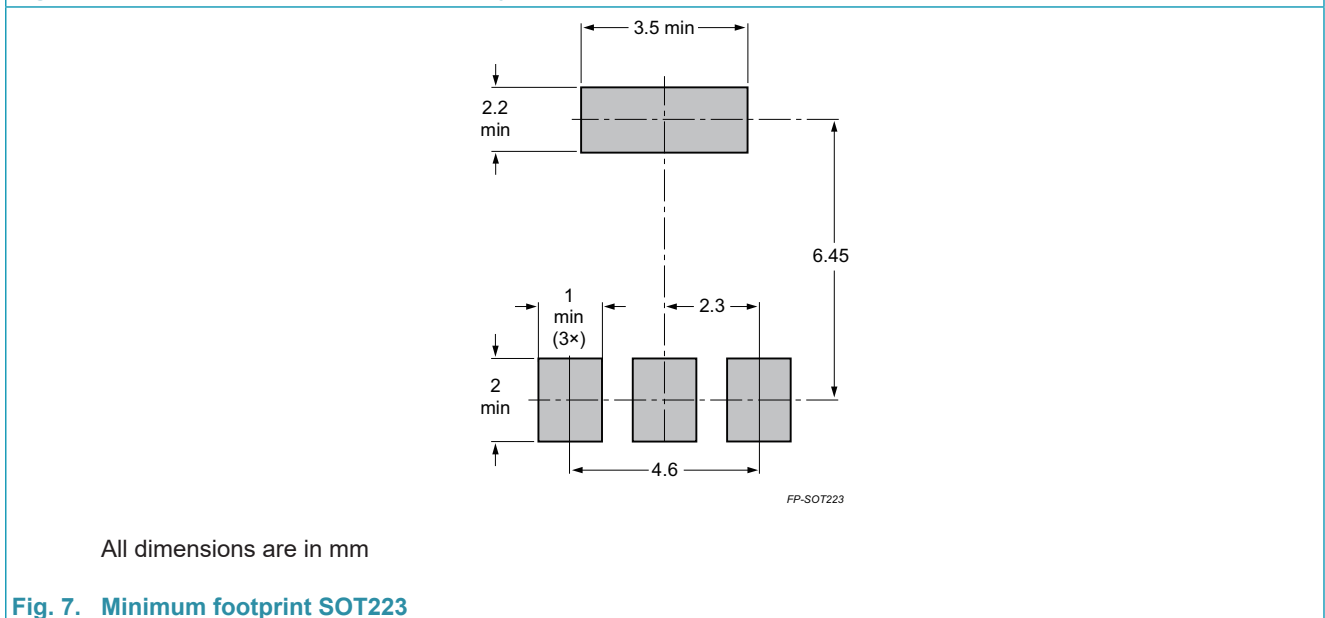


Fig. 6. Transient thermal impedance from junction to case as a function of pulse duration



All dimensions are in mm

Fig. 7. Minimum footprint SOT223

## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}; R_L = 140\ \Omega; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 8</a>	1	-	100	$\mu\text{A}$
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}; R_L = 140\ \Omega; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 12</a>	-	0.6	0.8	V
$V_{GD}$	gate non-trigger voltage	$V_D = V_{DRM}; R_L = 33\text{ k}\Omega; R_{GK} = 220\ \Omega; T_j = 125\text{ }^\circ\text{C}$	0.1	-	-	V
$V_{RG}$	gate reverse voltage	$I_{RG} = 2\text{ mA}; T_j = 25\text{ }^\circ\text{C}$	10	-	-	V
$I_L$	latching current	$I_T = 0.1\text{ A}; R_{GK} = 220\ \Omega; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 9</a>	-	-	12	mA
$I_H$	holding current	$V_D = 12\text{ V}; R_{GK} = 220\ \Omega; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 10</a>	-	-	10	mA
$V_T$	on-state voltage	$I_T = 2.5\text{ A}; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 11</a>	-	-	1.5	V
$I_D$	off-state current	$V_D = 1250\text{ V}; R_{GK} = 220\ \Omega; T_j = 25\text{ }^\circ\text{C}$	-	-	1	$\mu\text{A}$
		$V_D = 1250\text{ V}; R_{GK} = 220\ \Omega; T_j = 125\text{ }^\circ\text{C}$	-	-	100	$\mu\text{A}$
$I_R$	reverse current	$V_D = 1250\text{ V}; R_{GK} = 220\ \Omega; T_j = 25\text{ }^\circ\text{C}$	-	-	1	$\mu\text{A}$
		$V_D = 1250\text{ V}; R_{GK} = 220\ \Omega; T_j = 125\text{ }^\circ\text{C}$	-	-	100	$\mu\text{A}$
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 838\text{ V}; T_j = 125\text{ }^\circ\text{C}; R_{GK} = 220\ \Omega;$ ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform	200	-	-	V/ $\mu\text{s}$
$V_O$	threshold voltage	$T_j = 125\text{ }^\circ\text{C}$	-	-	0.936	V
$R_S$	dynamic resistance	$T_j = 125\text{ }^\circ\text{C}$	-	-	152	m $\Omega$

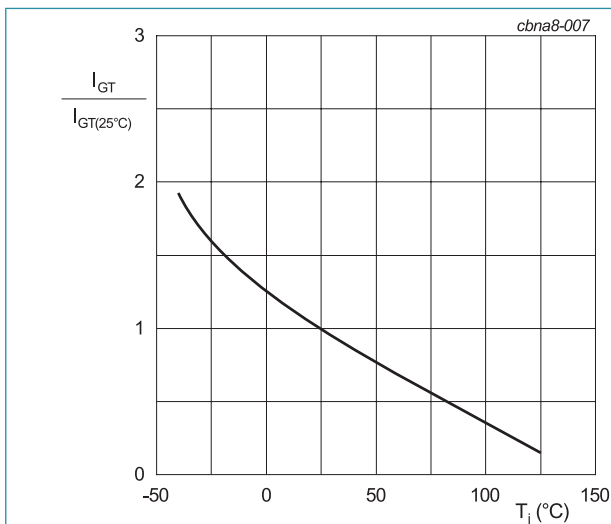


Fig. 8. Normalized gate trigger current as a function of junction temperature

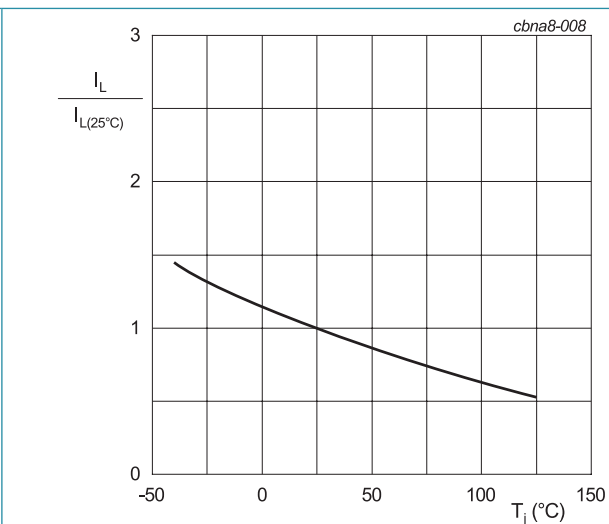
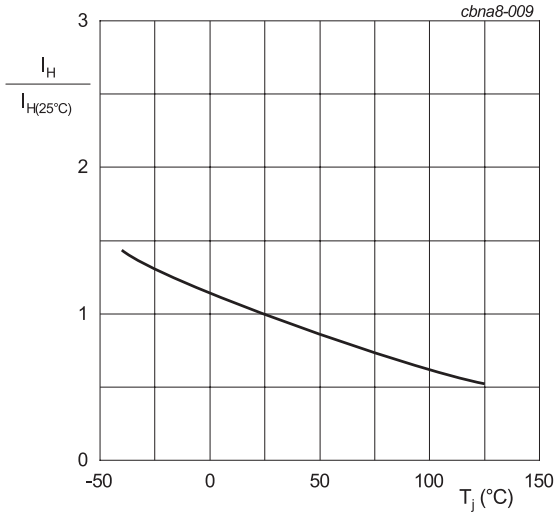
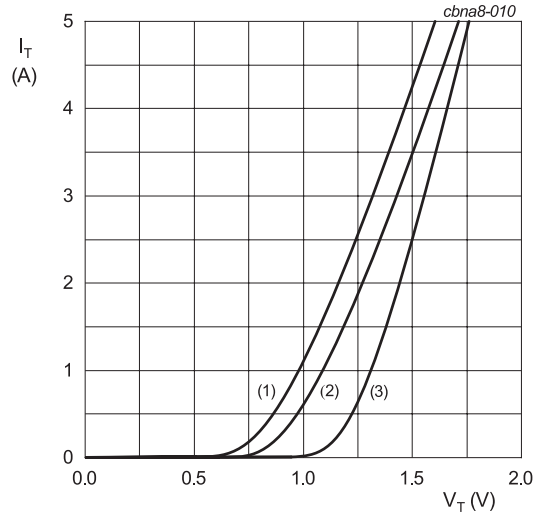


Fig. 9. Normalized latching current as a function of junction temperature

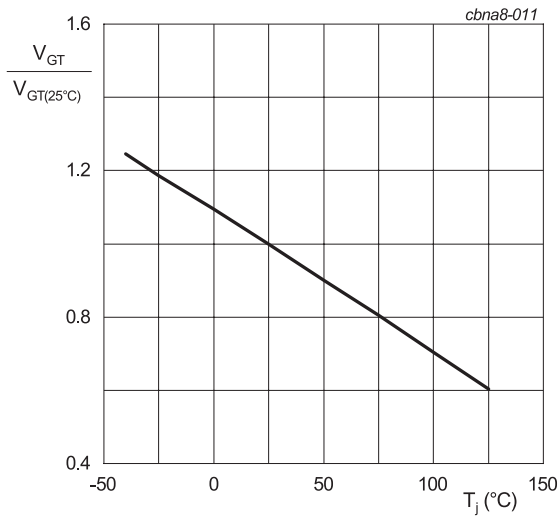


**Fig. 10. Normalized holding current as a function of junction temperature**



$V_o = 0.936 \text{ V}$ ;  $R_s = 0.1520 \Omega$   
 (1)  $T_j = 150 \text{ }^\circ\text{C}$ ; typical values  
 (2)  $T_j = 150 \text{ }^\circ\text{C}$ ; maximum values  
 (3)  $T_j = 25 \text{ }^\circ\text{C}$ ; maximum values

**Fig. 11. On-state current as a function of on-state voltage**



**Fig. 12. Normalized gate trigger voltage as a function of junction temperature**

## 11. AC line transient voltage ruggedness

NCR125W-125M has over voltage self-protected function, it can safely withstand AC line direct surge voltages by switching to on-state (for less than 10 ms on 50 Hz mains) to dissipate energy shocks through the load. The load limits the current through NCR125W-125M. The self-protection against over-voltage is based on an overvoltage crowbar technology. This safety feature works even with high turn-on current ramp up.

The NCR125W-125M recovers its blocking voltage capability after the direct surge and the next zero current crossing. Typical current and voltage as below according to the IEC 61000-4-5 standard conditions. Such a non-repetitive test can be done at least 10 times.

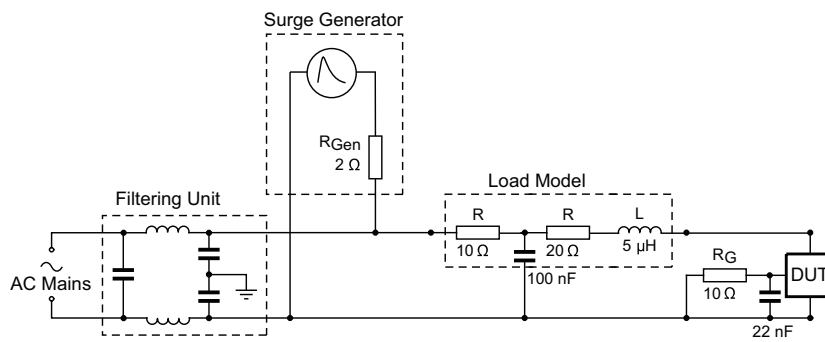


Fig. 13. Overvoltage ruggedness test circuit for IEC 61000-4-5 standards

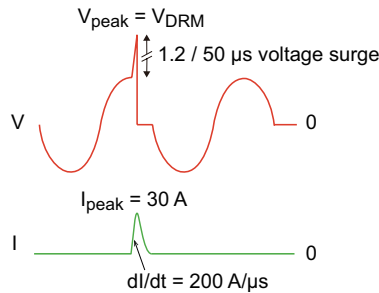
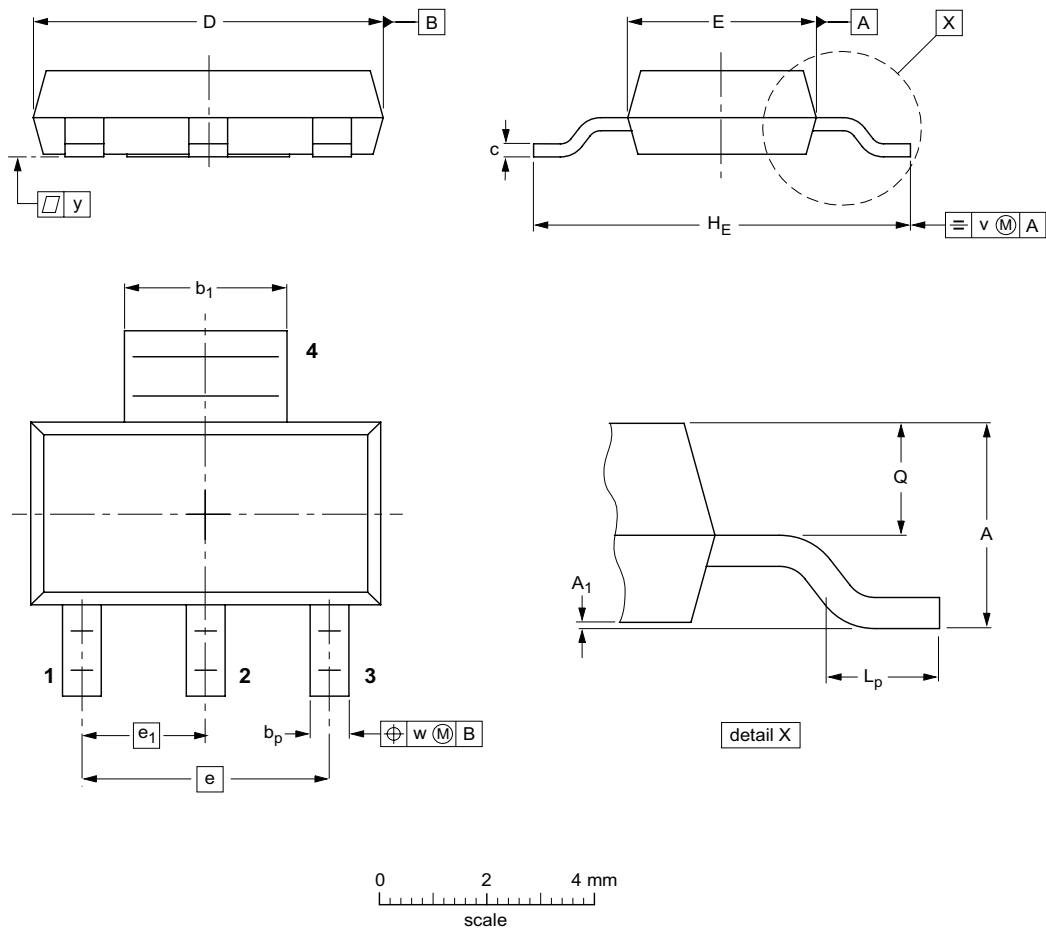


Fig. 14. Typical current and voltage waveforms across NCR125W-125M during IEC 61000-4-5 standard test

## 12. Package outline

Plastic surface-mounted package with increased heatsink; 4 leads

SOT223



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b <sub>p</sub>	b <sub>1</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w	y
mm	1.8 1.5	0.10 0.01	0.80 0.60	3.1 2.9	0.32 0.22	6.7 6.3	3.7 3.3	4.6	2.3	7.3 6.7	1.1 0.7	0.95 0.85	0.2	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT223			SC-73			04-11-10 06-03-16

Fig. 15. Package outline SOT223

## 13. Legal information

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## 14. Contents

---

1. General description.....	1
2. Features and benefits .....	1
3. Applications .....	1
4. Quick reference data.....	1
5. Pinning information.....	2
6. Ordering information.....	2
7. Marking.....	2
8. Limiting values .....	3
9. Thermal characteristics .....	5
10. Characteristics.....	6
11. AC line transient voltage ruggedness .....	8
12. Package outline .....	9
13. Legal information .....	10
14. Contents .....	12

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Date of release: 24 September 2019

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